IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

ENDOH et al.

Atty. Ref.: 900-397

Serial No. Unknown

Group:

Filed: August 10, 2001

Examiner:

For: A SEMICONDUCTOR MEMORY AND ITS PRODUCTION PROCESS

August 10, 2001

Assistant Commissioner for Patents Washington, DC 20231

Sir:

PRELIMINARY AMENDMENT

In order to place the above-identified application in better condition for examination, please amend the application as follows:

IN THE CLAIMS

Please substitute the following amended claims for corresponding claims previously presented. A copy of the amended claims showing current revisions is attached.

12. (Amended) A semiconductor memory according to claim 9, wherein the control gate and the gate electrode are disposed so closely that a channel layer located in a part of the island-like semiconductor layer opposed to the gate electrode is electrically connected to a channel layer of the memory cell.

14. (Amended) A semiconductor memory according to claim 9, wherein a plurality of memory cells are formed with regard to one island-like semiconductor layer, and an electrode for